## **Matchable Pairs – Emitter and Detector**

## **Description**

Pairs of infrared emitting diode and phototransistor, matched in their optical and electrical features. These pairs enable a lot of applications. They can be used both for transmissive or reflective sensor functions. The peak wavelength of the emitter is  $\lambda = 950$  nm.



## **Applications**

General for industrial processing and controlling; end of tape detector.

#### **Features**

- Subminiature case with lens
- Detector with optical filter, protected against ambient light
- Detector case black for easy identification of the emitter and detector
- Emitter-angle of half intensity  $\pm \varphi = 25^{\circ}$
- Detector-angle of half sensitivity  $\pm \varphi = 25^{\circ}$
- Emitter and detector in sideview case

#### **Pin Connection**

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# **Absolute Maximum Ratings**

## **Input (Emitter)**

Parameters	Test Conditions	Symbol	Value	Unit
Reserve voltage		$V_{R}$	6	V
Forward current		$I_{\mathrm{F}}$	60	mA
Forward surge current	t ≤ 10 μs	I <sub>FSM</sub>	1	A
Power dissipation	T <sub>amb</sub> ≤ 25°C	$P_{V}$	100	mW
Junction temperature		Tį	100	°C

# **Output (Detector)**

Parameters	Test Conditions	Symbol	Value	Unit
Collector-emitter voltage		$V_{CEO}$	70	V
Emitter-collector voltage		V <sub>ECO</sub>	7	V
Collector current		I <sub>C</sub>	50	mA
Peak collector current	$t_p/T = 0.5, t \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P <sub>V</sub>	150	mW
Junction temperature		Ti	100	°C

## **Emitter and Detector matched**

Parameters	Test Conditions	Symbol	Value	Unit
Ambient temperature range		T <sub>amb</sub>	-55 to +85	°C
Storage temperature range		T <sub>stg</sub>	-55 to +100	°C
Soldering temperature	2 mm from case, $t \le 5$ s	$T_{sd}$	260	°C

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## **Electrical Characteristics**

 $T_{amb} = 25^{\circ}C$ 

## **Input (Emitter)**

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	$V_{\mathrm{F}}$		1.25	1.6	V
Breakdown voltage	$I_R = 100 \mu A$	V <sub>(BR)</sub>	5			V

## **Output (Detector)**

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector-emitter break- down voltage	$I_C = 1 \text{ mA}$	V <sub>(BR)CEO</sub>	70			V
Emitter-collector break- down voltage	$I_E = 100 \mu A$	V <sub>(BR)ECO</sub>	7			V
Collector dark current	$V_{CE} = 25 \text{ V},$ $I_F = 0, E = 0$	I <sub>CEO</sub>			100	nA

#### **Emitter and Detector matched**

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector current	$I_F = 20 \text{ mA},$ $V_{CE} = 5 \text{ V}$	$I_{C}$	0.25	0.5		mA
	$V_{CE} = 5 \text{ V}$					
$I_{\rm C}/I_{\rm F}$	$   I_F = 20 \text{ mA}, $ $V_{CE} = 5 \text{ V} $	CTR	0.0125	0.025		
	$V_{CE} = 5 \text{ V}$					
Collector-emitter saturation	$I_F = 20 \text{ mA},$ $I_C = 25 \mu A$	V <sub>CEsat</sub>			0.4	V
voltage	$I_C = 25 \mu A$					
Cut-off frequency	$I_F = 10 \text{ mA},$	$f_c$		110		kHz
	$V_{CE} = 5 V$					
	$R_L = 100 \Omega$					

characteristics are measured at a separation distance of 4 mm (0.55") within a common axis of 0.5 mm (0.02") and parallel within 5°.

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# **Switching Characteristics**

 $V_S = 5 V$ 

Toma			$R_L = 10$	$R_L = 1 kΩ$ R <sub>L</sub> = 1 kΩ					1 $R_L = 1 \text{ k}\Omega$		
Туре	t <sub>d</sub> [μs]	t <sub>r</sub> [µs]	ton[µs]	t <sub>s</sub> [μs]	t <sub>f</sub> [µs]	t <sub>off</sub> [µs]	I <sub>C</sub> [mA]	ton[µs]	t <sub>off</sub> [µs]	I <sub>F</sub> [mA]	
TCZT8020			15			10	1				

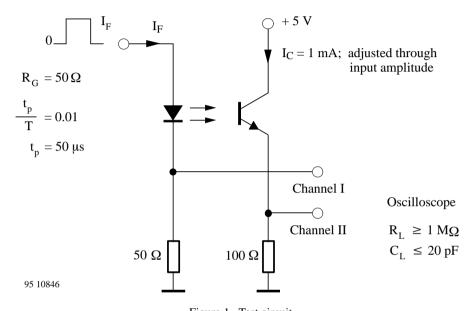


Figure 1. Test circuit

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#### **Ozone Depleting Substances Policy Statement**

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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